

ABSTRACT

The invention relates to the production of multilayered dielectric structures and to semiconductor devices and integrated circuits comprising these structures.

- 5 The structures of the invention are prepared by adhering a porous dielectric layer to a substantially nonporous capping layer via an intermediate adhesion promoting dielectric layer. A multilayered dielectric structure is prepared which has a porous dielectric layer which has a porosity of about 10% or more; b) an adhesion promoting dielectric layer on the porous dielectric layer
- 10 which has a porosity of about 10% or less; and a substantially nonporous capping layer on the adhesion promoting dielectric layer.